



**TO-251-3L Plastic-Encapsulate Transistors**

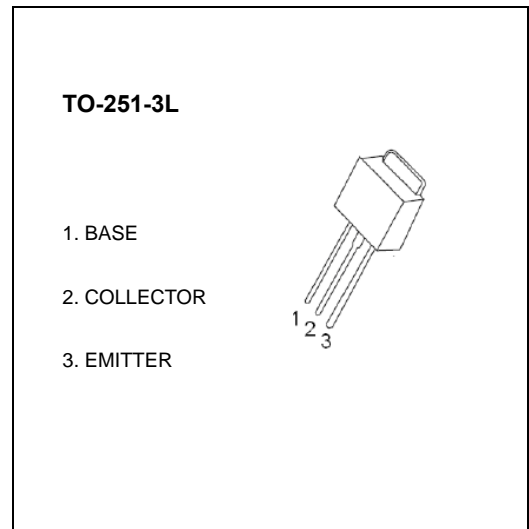
**2SD1760** TRANSISTOR (NPN)

**FEATURES**

- Low  $V_{CE(sat)}$
- Complements the 2SB1184

**MAXIMUM RATINGS** ( $T_a=25\text{ }^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	60	V
$V_{CEO}$	Collector-Emitter Voltage	50	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current -Continuous	3	A
$P_C$	Collector Power Dissipation	1.5	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55 to +150	$^\circ\text{C}$



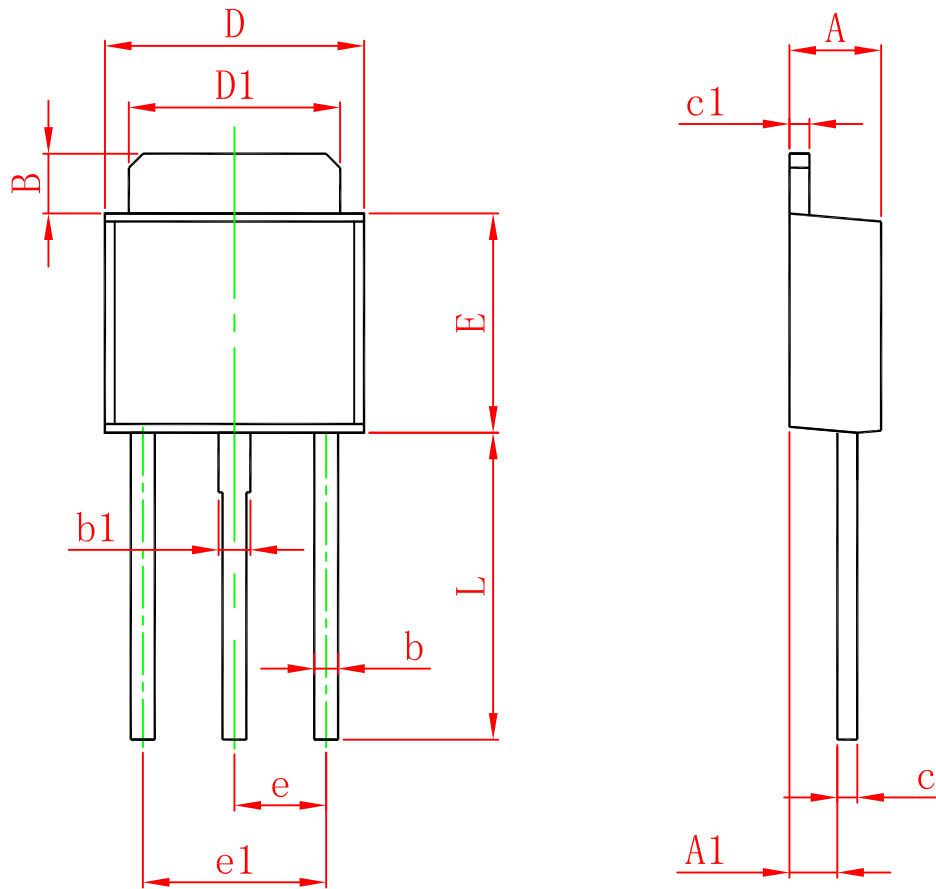
**ELECTRICAL CHARACTERISTICS** ( $T_a=25\text{ }^\circ\text{C}$  unless other wise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu\text{A}, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=40\text{V}, I_E=0$			1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=4\text{V}, I_C=0$			1	$\mu\text{A}$
DC current gain	$h_{FE\text{MIN}}$	$V_{CE}=3\text{V}, I_C=500\text{mA}$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2\text{A}, I_B=200\text{mA}$			1	V
Transition frequency	$f_T$	$V_{CE}=5\text{V}, I_C=500\text{mA}, f=30\text{MHz}$		90		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		40		pF

**CLASSIFICATION of  $h_{FE}$**

Rank	P	Q	R
Range	82-180	120-270	180-390

# TO-251-3L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	1.050	1.350	0.042	0.054
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	7.500	7.900	0.295	0.311